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Infrared absorption of GeNNO isolated in solid Ar

Zih-Min Jiang, 1 Joerg Glatthaar, 1,a) and Yuan-Pern Lee^{2,b)}

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Codeposition of thermally generated atomic germanium vapor and nitrous oxide (N₂O) in Ar onto a substrate at 11 K produced infrared absorption lines in several sets. The most prominent comprises intense lines at 1443.7, 1102.4, and 784.0 cm⁻¹ that become diminished upon irradiation with UV or visible light. These lines are attributed to ν_1 (NO stretching), ν_2 (NN+GeN stretching), and ν_3 (NNO bending+NN stretching) modes of singlet GeNNO. Two additional weak features at 1238.1 and 2859.2 cm⁻¹ are assigned as $\nu_3 + \nu_4$ and $2\nu_1$ of GeNNO, respectively. Weak doublet features at 1259.3/1255.5 and 1488.9/1486.4 cm⁻¹ are tentatively assigned to ν_2 of triplet GeONN and ν_1 of singlet cyc-Ge- η^2 [NN(O)], respectively. Quantum-chemical calculations on the Ge+N₂O system with density-functional theory (B3LYP /aug-cc-pVTZ) predict five stable structures: GeNNO (singlet and triplet), singlet cyc-Ge- η^2 [NN(O)], triplet cyc-Ge- η^2 (NNO), GeONN (singlet and triplet), and singlet GeNON. Vibrational wavenumbers, relative IR intensities, and ¹⁵N-isotopic ratios for observed species are consistent with those computed. Irradiation of singlet GeNNO with $\lambda = 248$ or 193 nm or $\lambda > 525$ nm yields GeO. © 2009 American Institute of Physics.

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I. INTRODUCTION

There is an increased attention to applications of oxides and nitrides of Ge in electronic devices. The greater mobility of carriers in germanium (Ge) than in silicon (Si) has promoted renewed interest in Ge-based high-performance logic devices.² SiGe p metal-oxide semiconductor fieldeffect transistor has attracted much attention because of the improved mobility and current drive capability. Si/Ge quantum dots embedded in an insulator have prospective applications not only for silicon-based optoelectronic devices having a large quantum efficiency for light emission^{4,5} but also for single-electron transistor memories at ambient temperature.^{6,7} With ultrahigh-vacuum chemical vapor deposition, Kim et al. demonstrated that annealing with N₂O is an important factor in the formation of Ge dots on insulators.⁸ Bera et al. also demonstrated that Si/Ge oxide films grown in a N₂O ambient have much improved leakage current, charge to breakdown, and breakdown field over those grown under pure O₂. A fundamental understanding of the reaction between Ge and N₂O is hence important in these processes.

The interactions of N_2O with Ge (111), disordered Ge (111), and amorphous Ge surfaces were studied near 300 K using high-resolution electron energy-loss spectroscopy (EELS), core-level and valence-band EELS, and Auger electron spectroscopy. 10 From these investigations, N2O molecules were found to decompose into desorbing N2 molecules and chemisorbed oxygen atoms.

The reported rate coefficients of the gaseous reaction $(1.2-9.9) \times 10^{-12}$ cm³ molecule⁻¹ s⁻¹ range $Ge + N_2O$ near 298 K^{11–14} and $(5.7–7.6) \times 10^{-12}$ cm³ molecule⁻¹ s⁻¹ near 580 K.^{13,15} Hager *et al.*¹⁶ and Capelle and Brom, Jr.¹⁷ detected emission from electronically excited states $a^{3}\Sigma^{+}$, $b^{3}\Pi_{1}$, and $A^{1}\Pi$ of GeO, designated GeO*, from reaction of Ge with N₂O. Fontijn and Felder reported that the order of GeO* photon yield was only 10⁻⁴. To explain these results, they proposed a mechanism involving a preferential reaction of Ge in its ${}^{3}P_{1}$ state with N₂O to form a "reservoir" GeO** state, from which the emitting GeO* states were produced via collision.

Theoretical calculations on the Ge+N₂O system, which focused on the formation of a GeONN complex and subsequent reactions, have been reported. 18 An argument based on electronic correlations among separated fragments Ge+O +N₂ was proposed to explain the inefficiency of the lowenergy adiabatic path from ground-state reactants $Ge(^{3}P)$ $+N_2O(^1\Sigma^+)$ to energetically accessible GeO+ $N_2(^1\Sigma_g^{\ +})$ product states. No other reaction channels of the reaction Ge +N₂O have been investigated either experimentally or theoretically.

Naulin *et al.* investigated the reaction of Si+N₂O using laser-induced fluorescence to detect SiN and deduced the existence of the product channel SiN+NO.¹⁹ The reaction intermediate trans-SiNNO was observed in a matrix codeposited from Si vapor and a gaseous mixture of N₂O and Ar.²⁰ One would expect that a similar reaction path also exists for the $Ge+N_2O$ reaction.

From the reaction of laser-ablated Ge with N2, we reported the production of GeNNGe isolated in solid Ar and its identification with infrared (IR) absorption.²¹ Using a similar

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method, we also observed matrix-isolated GeNO and ON-GeNO produced from reaction of laser-ablated Ge with NO.²² As a continuation of our investigation of reactions of Ge with small molecules, we report here the observation of IR absorption of singlet GeNNO and tentatively triplet GeONN and singlet cyc-Ge- η^2 [NN(O)], produced from the reaction of Ge with N₂O and their various ¹⁵N-labeled species.

II. EXPERIMENTS

The experimental setup is similar to one described previously; ^{21,22} we provide only brief descriptions here. An oven replaced the laser-ablation setup employed previously to generate gaseous atomic Ge vapor; the design of the oven developed by Maier *et al.* is described elsewhere. ²³ Approximately 4–10 mmol of a N₂O/Ar (1/150–1/300) mixture was codeposited with Ge vapor onto a cold Ni-plated Cu substrate for 0.5–1.0 h; the substrate was maintained at 11 K with a closed-cycle refrigerator (expander: Advanced Research Systems, model DE202A; compressor: APD Cryogenics, model HC-4MK).

Several light sources were employed to irradiate the matrix sample to induce photodissociation. Low-pressure and medium-pressure Hg lamps coupled with several optical filters of varied bandpass served as conventional light sources. A KrF excimer laser (248 nm, Lamda Physik, model LPX240i) and an ArF excimer laser (193 nm, Gam laser, model EX100H/60), both operated at 3 Hz with energies $\sim\!3\,$ mJ pulse $^{-1}$, were also employed at various stages of experiments.

IR absorption spectra were recorded with a Fourier-transform IR spectrometer (Bruker, model VERTEX-V80) equipped with a KBr beam splitter and a photovoltaic Hg/Cd/Te detector (77 K) to cover the spectral range 770–4000 cm⁻¹. Typically 200 scans at resolution of 0.5 cm⁻¹ were recorded at each stage of experiments.

A thermally shielded boron-nitride crucible (orifice of 3 mm) filled with Ge lumps (\sim 50 mg) was heated resistively with water-cooled electrodes (typical current \sim 45 A at 5 V) from a dc power supply (Good Will Instek, model PHS-10100A). Under these conditions the surface temperature of the molten Ge was estimated to be \sim 1430 K. Before the cryogenic compressor was turned on, the oven was slowly preheated to \sim 1430 K for 2 h until the pressure of the vacuum system dropped below 10^{-5} Torr to remove GeO from the Ge surface and trace adsorbates from the walls, followed by cooling the oven to 298 K before cooling the Ni-plated Cu substrate. After the substrate was cooled down to 11 K, the oven was heated to 1430 K in 3 min.

Gas mixtures of N₂O or its ¹⁵N-labeled isotopic variants with Ar (ratio of 1/150–1/300) were prepared with standard techniques. Ar (AGA Gases, 99.995%) was passed through a trap at 77 K to remove traces of water before mixing with N₂O. N₂O (Gas Standards Inc., 99.999%) was purified by degassing at 77 K. Various ¹⁵N-labeled N₂O were prepared by heating a solution of the corresponding ¹⁵N-labeled ammonium nitrate (NH₄NO₃, ~0.34 g) in concentrated H₂SO₄ (Riedel-de Haën, 95%–97%, 10–15 cm³) at ~463 K for

1.5 h under 500 Torr of dry N_2 . After the reaction, the reagents were cooled to 298 K and the gaseous products were trapped at 77 K. This crude N_2O sample was vaporized and further purified on condensation into a trap originally containing aqueous NaOH (5 cm³, ~5M, thoroughly degassed), followed by three freeze-pump-thaw cycles at 77 K to remove traces of N_2 , NO_2 , HNO_3 , and CO_2 . $^{14}NH_4$ $^{15}NO_3$, and $^{15}NH_4$ $^{15}NO_3$ (Cambridge Isotope Laboratories) have isotopic purities of 98M. Solid Ge (ABCR, Germany, 99.9999M) has a natural isotopic abundance ($^{70}Ge:20.38M$, $^{72}Ge:27.34M$, $^{73}Ge:7.75M$, $^{74}Ge:36.71M$, $^{76}Ge:7.82M$).

III. COMPUTATIONAL METHODS

The equilibrium geometries, energies, vibrational wavenumbers, and IR intensities were computed with the GAUSS-IAN 03 program. 26 Our calculations are based on B3LYP density-functional theory (DFT) that uses Becke's threeparameter hybrid exchange functional²⁷ and the Slater exchange functional with corrections involving a gradient of the density and a correlation functional of Lee, Yang, and Parr, with both local and nonlocal terms.²⁸ Dunning's correlation-consistent polarized valence triple-zeta basis set augmented with s, p, d, and f functions (aug-cc-pVTZ)²⁹ and the standard split valence 6-311G basis for first-row atoms and the McLean-Chandler (12s, 9p) (631111, 52111) basis sets for second-row atoms including p, d, and diffuse functions [designated 6-311+G(d,p)] were used. ^{30,31} For the description of a germanium atom the Wood-Boring quasirelativistic effective core potential^{32–34} MWB28 of the Stuttgart/ Dresden theoretical group, replacing 28 core electrons by a pseudopotential, was applied. Analytic first and second derivatives were applied for geometry optimization and vibrational wavenumbers at each stationary point.

IV. EXPERIMENTAL RESULTS

A. Reactions of Ge with N₂O

The IR spectrum of a sample of N_2O/Ar (1/300) at 11 K exhibits intense lines at 1282.8 (ν_1) and 2218.6 (ν_3) cm⁻¹ and weak lines at 1167.5 $(2\nu_2)$, 2459.6 $(\nu_1+2\nu_2)$, 2559.2 $(2\nu_1)$, 3358.6 $(2\nu_2+\nu_3)$, and 3473.6 $(\nu_1+\nu_3)$ cm⁻¹ due to N₂O; a partial spectrum is shown in trace (a) of Fig. 1. Extremely weak lines of N_2O at 1245.0 (ν_1 of $^{14}N^{14}N^{18}O$), 1878.1/1879.1 ($\nu_1 + \nu_2$), 2211.7 (ν_3 of $^{14}N^{14}N^{18}O$), and 2793.0 $(\nu_2 + \nu_3)$ cm⁻¹ were also identified. The two most intense features of N2O split into multiplets with additional lines at 2227.5, 2226.3, 2224.4, 2222.7, 2215.4, 2214.2, and 2213.0 cm⁻¹ for ν_3 and 1287.6, 1286.1, 1278.7, and 1277.7 cm⁻¹ for ν_1 . The IR spectrum of a sample deposited at 11 K from reaction of atomic Ge vapor with a flowing gaseous mixture of N₂O/Ar (1/300) exhibits a set of new features with intense lines at 1443.7, 1102.4, and 784.0 cm⁻¹ and much weaker features at 2859.2, 1488.9/1486.4, 1259.3/ 1255.5, and 1241.8/1239.7/1238.1 cm⁻¹, as indicated in trace (b) of Fig. 1.

Additional weak features at 2345.1 and 2339.2 cm⁻¹ due to CO_2 , 2138.4 cm⁻¹ due to CO, 2122.9, 2113.9, and

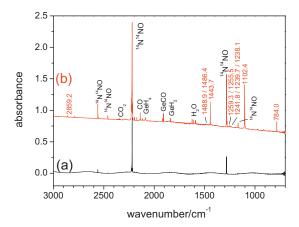


FIG. 1. IR spectra following (a) codeposition at 11 K of a gaseous mixture of N_2O in Ar (1/300) for 5 min and (b) codeposition at 11 K of a gaseous mixture of N_2O in Ar (1/300) with atomic Ge vapor for 1 h. The wavenumbers of new IR signals due to reaction products of Ge and N_2O are listed; the signals of impurities caused by the heating of the crucible are labeled.

2087.4 cm $^{-1}$ due to GeH $_4$, 35,36 1919.0 and 1907.6 cm $^{-1}$ due to GeCO, $^{37-39}$ 1839.0 and 913.4 cm $^{-1}$ due to GeH $_2$, 36 1814.4 due to GeH $_2$ 0 for 36 1576.9 cm $^{-1}$ due to GeH $_2$ 0, 40 and two unidentified lines at 947.7 and 918.5 cm $^{-1}$ are unrelated to reactions with N $_2$ 0 because these features were also observed when a stream of Ge atoms was codeposited with pure Ar under similar experimental conditions. These additional features, except the line at 1576.9 cm $^{-1}$ due to GeH $_2$ 0, did not change in intensity upon photoirradiation; these additional features remain unaltered in position also when 15 N-labeled N $_2$ 0 was used.

The new features observed from reactions of Ge with N_2O can be organized into several groups according to their photolytic behaviors. Upon irradiation of the matrix with 248-nm laser emission for 5 min or with a medium-pressure Hg lamp combined with a GG525 cutoff filter (pass band $\lambda > 525$ nm) for 2 h, new intense features (group A) at 1443.7, 1102.4, and 784.0 cm⁻¹ together with weak lines at 2859.2 (not shown) and 1238.1/1239.7/1241.8 cm⁻¹ diminished nearly completely, whereas the quintet lines of GeO near 975 cm⁻¹ increased in intensity, as shown in trace (b) of Fig. 2 as a difference spectrum. In these difference spectra, lines

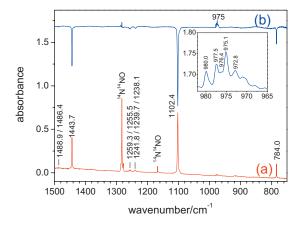


FIG. 2. (a) Partial IR spectrum in the region 750–1500 cm $^{-1}$ recorded after codeposition of Ge and N_2O in Ar (same as trace b of Fig. 1) and (b) difference spectrum after irradiation at 248 nm (KrF laser, 3 Hz, 3.3 mJ pulse $^{-1}$, 5 min).

pointing upwards indicate production, whereas those pointing downwards indicate destruction. The quintet lines observed at 980.0, 977.5, 976.4, 975.1, and 972.8 cm⁻¹ correspond to well characterized absorption of GeO with isotopic splitting and relative intensities consistent with natural abundance of Ge isotopes as indicated above, 21,41 except for redshifts of 1.6-1.9 cm⁻¹ for the latter due to interactions with nearby N₂. Trace (a) of Fig. 2 is the spectrum of Ge+N₂O in solid Ar before photoirradiation. The weak doublet feature at 1259.3 and 1255.5 cm⁻¹ (group B) diminished rapidly only upon irradiation with $\lambda \le 248\,$ nm, but its intensity remained unchanged with $\lambda > 525$ nm irradiation. The extremely weak doublet feature at 1488.9 and 1486.4 cm⁻¹ (group C) slowly diminished upon irradiation with $\lambda \le 248$ nm but increased in intensity slightly in the initial (t < 30 min) stage of irradiation with $\lambda > 525$ nm, followed by slow decrease in intensity.

The formation of new features upon photolysis at 248 or 254 nm (emission of the low-pressure Hg lamp) is much faster than when 193 nm laser emission was applied. Additional lines at 1863.9 and 1776.3 cm⁻¹, which increased in intensity continuously, are readily assigned as $cis-N_2O_2$; 42,43 they were observed also when N₂O in Ar was deposited at 11 K in the absence of Ge and irradiated under the same conditions. A second group of lines at 1759.1, 1744.9, and 1740.9 cm⁻¹ increases rapidly in intensity at the initial stage of irradiation but attained their maximal intensities within 30 min. The first two features are photolysis products of the GeH₂O complex, assigned as HGeO and HGeOH, ⁴⁰ respectively; the 1740.9 cm⁻¹ line is new. These lines did not shift when ¹⁵N-labeled N₂O was used. They were also observed when Ge in Ar was deposited in the absence of N2O and irradiated under the same conditions.

B. Reaction of Ge with ¹⁵N-labeled N₂O

When isotopically labeled 15 N¹⁴NO replaced 14 N¹⁴NO, the two main lines of 14 N¹⁴NO shifted to 1267.9 (ν_1) and 2196.4 (ν_3) cm⁻¹, and weak features shifted to 1159.6 ($2\nu_2$), 1239.8 (ν_1 of 15 N¹⁴N¹⁸O), 1860.8/1861.8 ($\nu_1+\nu_2$), 2189.0 (ν_3 of 15 N¹⁴N¹⁸O), 2530.8 ($2\nu_1$), 2767.5 ($\nu_2+\nu_3$), 3328.4 ($2\nu_2+\nu_3$), and 3436.5 ($\nu_1+\nu_3$) cm⁻¹. Additional multiple lines of the two most intense features of 15 N¹⁴NO are at 2204.9, 2203.9, 2201.3, 2200.0, 2193.1, 2192.1, and 2191.0 (ν_3) cm⁻¹ and 1272.4, 1270.4, 1264.0, and 1263.2 (ν_1) cm⁻¹.

Upon reaction with Ge, the new lines in group A shifted to 2850.9, 1440.2, 1231.2/1232.5/1234.5, 1074.7, and 778.7 cm $^{-1}$. Those in group B shifted to 1244.6 and 1241.8 cm $^{-1}$ and those in group C to 1486.7 and 1484.2 cm $^{-1}$. A partial difference spectrum upon irradiation at 248 nm is shown in trace (b) of Fig. 3 for comparison with results of Ge+ 14 N 14 NO (trace a); the difference spectra of the matrices upon 248 nm laser irradiation are shown to indicate the species produced (positive lines) or destroyed (negative lines) upon irradiation. The photochemical behaviors of these features are the same as those observed in the Ge+ 14 N 14 NO experiment.

When isotopically labeled $^{14}N^{15}NO$ replaced $^{14}N^{14}NO$, lines of $^{14}N^{14}NO$ shifted to 1143.6 (2 ν_2), 1238.3 (ν_1 of

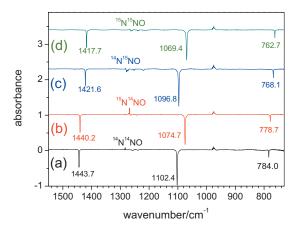


FIG. 3. Difference spectra of matrices codeposited with Ge and various $^{15}\text{N-labeled N}_2\text{O}$ upon irradiation at 248 nm: (a) $^{14}\text{N}^{14}\text{NO}$, (b) $^{15}\text{N}^{14}\text{NO}$, (c) $^{14}\text{N}^{15}\text{NO}$, and (d) $^{15}\text{N}^{15}\text{NO}$.

 $^{14}\mathrm{N}^{15}\mathrm{N}^{18}\mathrm{O}),\ 1278.2\ (\nu_1),\ 1857.9/1858.7\ (\nu_1+\nu_2),\ 2166.1\ (\nu_3)$ of $^{14}\mathrm{N}^{15}\mathrm{N}^{18}\mathrm{O}),\ 2172.5\ (\nu_3),\ 2548.1\ (2\nu_1),\ 2734.7\ (\nu_2+\nu_3),\ 3290.0\ (2\nu_2+\nu_3),\ and\ 3425.0\ (\nu_1+\nu_3)\ cm^{-1}.$ The two most intense fundamentals of $^{14}\mathrm{N}^{15}\mathrm{NO}$ show additional lines at 2181.5, 2180.3, 2178.4, 2176.9, 2169.7, 2168.5, and 2167.2 $(\nu_3)\ cm^{-1},\ and\ 1282.7,\ 1281.5,\ 1274.1,\ and\ 1272.8\ (\nu_1)\ cm^{-1}.$ Upon reaction with Ge, the new lines in group A shifted to 2816.6, 1421.6, 1219.1/1220.8/1222.7, 1096.8, and 768.1 cm⁻¹, those in group B shifted to 1254.6 and 1250.9 cm⁻¹, and those in group C shifted to 1458.7 and 1456.2 cm⁻¹. A partial difference spectrum upon irradiation at 248 nm is shown in trace (c) of Fig. 3.

When isotopically labeled 15 N 15 NO replaced 14 N 14 NO, lines of 14 N 14 NO shifted to 1135.9 (2 ν_2), 1224.1 (ν_1 of 15 N 15 N 18 O), 1263.2 (ν_1), 1841.1 ($\nu_1+\nu_2$), 2142.4 (ν_3 of 15 N 15 N 18 O), 2149.6 (ν_3), 2519.1 (2 ν_1), 2708.3 ($\nu_2+\nu_3$), 3259.0 (2 $\nu_2+\nu_3$), and 3387.1 ($\nu_1+\nu_3$) cm $^{-1}$. The most intense fundamentals of 15 N 15 NO are split into multiplets with additional lines at 2158.1, 2157.1, 2155.2, 2153.5, 2146.5, 2145.3, and 2144.3 cm $^{-1}$ (ν_3) and 1268.0, 1266.3, 1259.4, and 1258.2 cm $^{-1}$ (ν_1). Upon reaction with Ge, the new lines in group A shifted to 2808.0, 1417.7, 1211.3/1213.1/1215.1, 1069.4, and 762.7 cm $^{-1}$, those in group B shifted to 1240.6 and 1237.1 cm $^{-1}$, and those in group C shifted to 1456.4 and 1454.1 cm $^{-1}$. A partial difference spectrum upon irradiation at 248 nm is shown in trace (d) of Fig. 3.

The observed wavenumbers of these new features from the reaction of Ge with various 15 N-labeled N_2 O are summarized in Table I. As the positions of lines assigned to GeO remain unaltered when such labeled N_2 O were used, they are not listed in Table I.

V. RESULTS OF QUANTUM-CHEMICAL COMPUTATIONS

A. Energies and geometries of GeN₂O isomers

With theoretical calculations according to B3LYP DFT and aug-cc-pVTZ and 6-311+G(d,p) basis sets, we located five isomers of GeN₂O: GeNNO (in singlet and triplet electronic states), cyc^{-1} Ge- η^2 [NN(O)], cyc^{-3} Ge- η^2 (NNO), GeONN (in singlet and triplet electronic states), and 1 GeNON; we indicate singlet and triplet electronic states

TABLE I. Vibrational wavenumbers (cm $^{-1}$) of new lines observed upon codeposition of Ge vapor with a mixture of N₂O/Ar (1/200) at 11 K.

Group	Species	Mode	¹⁴ N ¹⁴ NO	$^{15}N^{14}NO$	$^{14}N^{15}NO$	¹⁵ N ¹⁵ NO
A	¹ GeNNO	ν_1	1443.7	1440.2	1421.6	1417.7
				$(0.9976)^{a}$	$(0.9847)^{a}$	$(0.9820)^{a}$
		ν_2	1102.4	1074.7	1096.8	1069.4
				(0.9749)	(0.9949)	(0.9701)
		ν_3	784.0	778.7	768.1	762.7
				(0.9932)	(0.9797)	(0.9728)
		$\nu_3 + \nu_4$	1241.8 ^b	1234.5 ^b	1222.7 ^b	1215.1 ^b
				(0.9941)	(0.9846)	(0.9785)
			1239.7	1232.5	1220.8	1213.1
				(0.9942)	(0.9848)	(0.9785)
			1238.1	1231.2	1219.1	1211.3
				(0.9944)	(0.9847)	(0.9784)
		$2\nu_1$	2859.2	2850.9	2816.6	2808.0
				(0.9971)	(0.9851)	(0.9821)
В	³ GeONN	$ u_2$	1259.3	1244.6	1254.6	1240.6
				(0.9883)	(0.9963)	(0.9852)
			1255.5	1241.8	1250.9	1237.1
				(0.9891)	(0.9963)	(0.9853)
C	$cyc^{-1}Ge^{-\eta^2}$ [NN(O)]	$ u_1$	1488.9	1486.7	1458.7	1456.4
				(0.9985)	(0.9797)	(0.9782)
			1486.4	1484.2	1456.2	1454.1
				(0.9985)	(0.9797)	(0.9783)

^aThe isotopic ratio, defined as the ratio of vibrational wavenumber of the specific isotopic variant to that of the naturally abundant species containing ⁷⁴Ge, ¹⁴N, and ¹⁶O are listed in parentheses.

^bThe first two lines correspond to ⁷⁰Ge and ⁷²Ge species and the third one to an unresolved contribution of ⁷³Ge

^bThe first two lines correspond to ⁷⁰Ge and ⁷²Ge species and the third one to an unresolved contribution of ⁷³Ge and ⁷⁴Ge species.

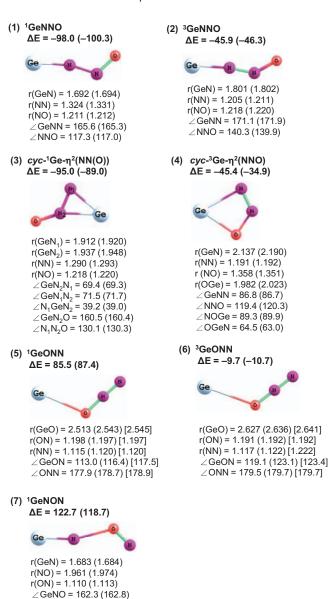


FIG. 4. Geometries and relative energies of stable GeN_2O isomers computed with B3LYP/aug-cc-pVTZ and B3LYP/6-311+G(d,p) methods. Bond lengths are in Å, bond angles in degrees, and relative energies in kJ mol⁻¹. Values derived from B3LYP/6-311+G(d,p) are listed in parentheses. Those reported previously (Ref. 18) using B3LYP/6-311+ G^* are listed in brackets.

 \angle NON = 119.8 (119.9)

with superscripts "1" and "3," respectively, before "Ge." ¹GeONN and ¹GeNON are unlikely to be produced from ³Ge+N₂O because they have energies greater than the reactants. Figure 4 shows the geometries and relative energies (zero-point energy corrected) of these isomers, respectively; values from B3LYP/6-311+G(d,p) computations are listed in parentheses. The reference energy is Ge+N₂O at -2261.73483hartree for B3LYP/aug-cc-pVTZ -2261.63850 hartree for B3LYP/6-311+G(d,p). Energies, zero-point energies, and relative energies of GeN₂O isomers predicted with B3LYP/aug-cc-pVTZ and B3LYP/6-311 +G(d,p) are available from the Electronic Physics Auxiliary Publication Service (EPAPS).44

According to computations with B3LYP/aug-cc-pVTZ, the planar 1 GeNNO has the least energy, -98.0 kJ mol $^{-1}$, relative to Ge+N $_{2}$ O. The N-O bond length is 1.211 Å,

slightly greater than that of NO (1.151 Å). ⁴⁵ The Ge–N bond length of 1.692 Å is slightly smaller than those for GeNO (1.785 Å) (Ref. 22) predicted at BLYP/aug-cc-pVTZ and GeNNGe (1.709 Å) (Ref. 21) predicted at B3LYP/aug-cc-pVTZ. The N–N bond length of 1.324 Å is 0.084 Å greater than that of GeNNGe (1.240 Å) predicted at the same level of theory. ²¹

The ground electronic state of GeNNO is singlet $(^1A')$; its electronically excited triplet state $(^3A'')$ lies 52.1 kJ mol $^{-1}$ above the ground state. The main difference in geometry between $^1\text{GeNNO}$ and $^3\text{GeNNO}$ is that the ONN moiety of the latter is less bent and the length of the N–N bond decreases from 1.324 Å in the ground singlet state to 1.205 Å in its triplet state, and the length of the Ge–N bond increases from 1.692 to 1.801 Å.

The planar C_s -symmetric cyc^{-1} Ge- η^2 [NN(O)], with Ge and two N atoms forming a three-membered ring, has energy of -95.0 kJ mol⁻¹, slightly greater than that of 1 GeNNO. The two Ge–N bonds in the slightly asymmetric three-membered ring are 1.912 (Ge– N_1) and 1.937 Å (Ge– N_2), indicating a slightly stronger bond of Ge to the terminal nitrogen of the NNO moiety. The GeN₂ ring is stabilized via an electron-withdrawing (–I) effect of the oxygen substituent at N₂. Both Ge–N bonds are shorter than the computed bond length of 2.023 Å for Ge–N bonds in cyc-GeN₂, 21 whereas the N–N bond length of 1.290 Å is much larger than the N–N bond in cyc-GeN₂ (1.195 Å). The NGeN angle of 39.2° is larger than the NGeN angle of 34.4° in cyc-GeN₂.

On the corresponding triplet energy surface, $cyc^{-3}Ge^{-\eta^2}$ (NNO) has energy of -45.4 kJ mol⁻¹ below Ge+N₂O, similar to that of ³GeNNO. The NNO moiety is bent (119.4°) with elongated N-N (1.191 Å) and N-O (1.358 Å) bonds relative to free NNO (N-N: 1.125 Å, N-O: 1.185 Å).

 3 GeONN(3 A) with energy of -9.7 kJ mol $^{-1}$ relative to Ge+N $_2$ O may be considered as a complex with 3 Ge attaching the O atom of N $_2$ O. The Ge–O bond length of 2.627 Å, the GeON bond angle of 119.1°, and the almost linear ONN moiety indicate a weak interaction between 3 Ge and the O atom. The N–O bond length of 1.191 Å is slightly longer than the N–O bond in NNO (1.185 Å). The N–N bond length of 1.117 Å is 0.008 Å shorter than that for NNO (1.125 Å) predicted at the B3LYP/aug-cc-pVTZ level.

The singlet electronically excited state of GeONN, 1 GeONN, may be considered as a complex with 1 Ge attaching the O atom of N₂O; its energy is 85.5 kJ mol⁻¹ above 3 Ge+N₂O. The Ge–O bond length of 2.513 Å, the GeON bond angle of 113.0°, and the almost linear (177.9°) ONN moiety indicates a slightly stronger interaction between 1 Ge and the O atom in 1 GeONN relative to that between 3 Ge and O in 3 GeONN (Ge–O, length of 2.627 Å). Previous computations 18 on both singlet and triplet states of GeONN using B3LYP/6-311+G*, listed in brackets in Fig. 4, are consistent with our results.

GeNON ($^{1}A'$) is the least stable isomer of GeN₂O, with energy of 122.7 kJ mol⁻¹ above 3 Ge+N₂O. The Ge–N bond length of 1.683 Å is slightly shorter than that of 1 GeNNO (1.692 Å). The terminal N–O bond length of 1.110 Å is 0.1

Å shorter than that of ¹GeNNO, whereas the central N–O bond length of 1.961 Å indicates weak bonding between the GeN and NO moieties.

B. Vibrational wavenumbers and IR Intensities of GeN₂O isomers

Vibrational wavenumbers and IR intensities for each isomer calculated with B3LYP/aug-cc-pVTZ B3LYP/6-311+G(d,p) are listed in Table II. For ¹GeNNO, two intense IR absorption lines at 1511 (ν_1 , NO stretch) and 1165 (ν_2 , NN+GeN stretch) cm⁻¹ and a weaker absorption at 773 (ν_3 , NNO bend+NN stretch) cm⁻¹ are predicted. The force constant of 11.6 mdyne Å⁻¹ for the Ge-N bond indicates some double-bond character. For ³GeNNO, two intense IR lines of similar intensities at 1712 (ν_1 , NNO a-stretch) and 1186 (ν_2 , NNO s-stretch) cm⁻¹ are within the range of our detection. The weaker interaction of the Ge atom with the terminal nitrogen of the NNO moiety in ³GeNNO produces blueshifts of these two lines compared with ¹GeNNO.

 cyc^{-1} Ge- η^2 [NN(O)] is predicted to show an intense absorption near 1550 cm⁻¹ (ν_1 , NO stretch). The other absorption lines within the range of our detection are predicted to be weak. Because of the increased bond length, the N–N stretching mode is red-shifted to 1190 cm⁻¹ for comparison with cyc-GeN₂ (1662 cm⁻¹). In contrast, cyc- 3 Ge- η^2 (NNO) is predicted to show an intense line at 1654 cm⁻¹ (ν_1 , NN stretch) and a medium one at 847 cm⁻¹ (ν_2 , NO stretch).

 3 GeONN and 1 GeONN are expected to have similar IR absorption patterns. In the range of our detection, lines at 2346 (ν_1 , NNO a-stretch) and 1296 (ν_2 , NNO s-stretch) cm⁻¹ are predicted for 3 GeONN, and 2347 (ν_1) and 1257 (ν_2) cm⁻¹ for 1 GeONN. The blueshift of the ν_1 mode and the redshift of the ν_2 mode compared with free N₂O (ν_1 = 2306.7 cm⁻¹ and ν_2 =1314.1 cm⁻¹) are consistent with the changes in the geometry of the ONN moiety due to the complex formation with the Ge atom.

For GeNON, two intense vibrational modes are predicted at 2000 (ν_1 , NO stretch) and 977 (ν_2 , GeN stretch) cm⁻¹. The NO stretch is blueshifted relative to free NO (1968 cm⁻¹) by 32 cm⁻¹, and the GeN stretch is blueshifted by 26 cm⁻¹ relative to free GeN (951 cm⁻¹). Both effects are explicable according to a slightly positive charge of the NO moiety, causing a larger force constant (35.0 versus 33.9 mdyne Å⁻¹ for free NO) and by the slightly negatively charged GeN moiety, causing a stronger attraction between Ge and N atoms (force constant of 8.84 versus 8.57 mdyne Å⁻¹ for free GeN).

Vibrational wavenumbers of these species containing one or two $^{15}\mathrm{N}$ or one $^{72}\mathrm{Ge}$ were also computed and presented as isotopic ratios in Table II. The isotopic ratio is defined as the ratio of vibrational wavenumber of the specific isotopic variant to that of the naturally abundant species, in this case, species containing $^{74}\mathrm{Ge}$, $^{14}\mathrm{N}$, and $^{16}\mathrm{O}$.

C. Reaction paths of Ge+N₂O

Reaction paths and energies of the transition states and stable species on the GeN₂O potential energy surface computed with B3LYP/aug-cc-pVTZ are shown in Fig. 5. Com-

puted energies and geometries of relevant transition states TS1–TS8 are available from the EPAPS. When 3 Ge and N_2 O approach closely, at least six scenarios might be considered. The Ge atom might interact with the terminal oxygen atom, the terminal nitrogen, or the central nitrogen atom of N_2 O. Alternatively, the Ge atom might interact simultaneously with two nitrogen atom or the oxygen atom and one nitrogen atom in either the central or terminal position.

Interaction between the oxygen atom and the Ge atom is slightly attractive; with no activation a $^3\text{GeONN}$ complex is formed. $^3\text{GeONN}$ is further connected via TS1 (E_A = 22.0 kJ mol $^{-1}$) to a reaction path forming ^3GeO and N $_2$. The TS1 transition state having a *trans*-like structure is more than 10 kJ mol $^{-1}$ lower in energy at the B3LYP/6-311 +G(d,p) level of theory than the transition state with a *cis*-like structure that was reported previously by Wang *et al.* ¹⁸ This *cis*-like transition state has a structure almost identical to TS2 (see Fig. S1 in EPAPS); TS2 connects between ^3Ge +N $_2\text{O}$ and cyc- ^3Ge - η^2 (NNO) but not connects to the reaction pathway leading to ^3GeO and N $_2$. All considerations and conclusion derived based on this transition state in Ref. 18 might be in error.

Interaction between the terminal nitrogen of N_2O and 3Ge is strongly exothermic yielding with no activation directly a stable 3GeNNO complex with a short GeN bond length of 1.801 Å. In contrast, interaction between the central nitrogen atom and 3Ge is repulsive, even if the initial NNO skeleton geometry is slightly bent. During the optimization the Ge atom becomes oriented toward the terminal nitrogen but eventually forms the stable 3GeNNO .

The same argument is applicable for the interaction between ³Ge and the two neighboring nitrogen atoms. No stable triplet structure containing a three-membered GeNN ring was located. The bond between the central nitrogen and the germanium atom opened and the structure collapsed into the more stabilized ³GeNNO. The most important reaction channel of ³GeNNO occurs on intersystem crossing to the more stable ³GeNNO (–98.0 kJ mol⁻¹); the two structures are similar. The path to generate GeN and NO from ³GeNNO has a high barrier via transition state TS5 at 133.7 kJ mol⁻¹.

Interaction between 3 Ge and both terminal nitrogen and oxygen atoms is an endothermic process, because the NNO unit must become bent to accomplish a doubly stabilizing interaction between Ge, O, and N atoms. Transition state TS2 forming cyc^{-3} Ge- η^{2} (NNO) has energy of 25.5 kJ mol⁻¹ greater than the initial 3 Ge+N₂O. cyc-Ge- ${}^{3}\eta^{2}$ (NNO) is further connected to 3 GeNNO (-45.9 kJ mol⁻¹) via transition state TS3 with a barrier of 36.4 kJ mol⁻¹. A third transition state TS4 (-37.7 kJ mol⁻¹) with a barrier of 7.7 kJ mol⁻¹ leads to the formation of 3 GeO and N₂.

 3 GeNNO has several reaction channels. It might dissociate to form GeO+N₂ via a *s-cis* symmetric transition state TS6 located at -46.3 kJ mol⁻¹; the barrier of 51.7 kJ mol⁻¹ represents the smallest among known reaction paths of 1 GeNNO. A second transition state TS7 at energy -30.8 kJ mol⁻¹ precedes formation of cyc^{-1} Ge- η^2 [NN(O)]; the GeNN angle decreases from 165.6° to 99.1° . The reaction path leading to 1 GeNON via transition state TS8 (162.8 kJ mol⁻¹) exhibits a large barrier.

TABLE II. Vibrational wavenumbers (σ), IR intensities (km mol⁻¹), and isotopic ratios of seven stable species of GeN₂O predicted with B3LYP/aug-cc-pVTZ and B3LYP/6-311+G(d,p).

			Absorption		Isotopic ratio ^a			
ν_i	Symmetry	Mode	σ (cm ⁻¹)	IR intensities	¹⁵ N ¹⁴ NO	¹⁴ N ¹⁵ NO	¹⁵ N ¹⁵ NO	⁷² Ge
	eNNO							
ν_1	A'	NO stretch	1510.6 (1523.5) ^b	243.5 (258.2) ^b	0.9984 (0.9985) ^b	0.9842 (0.9841) ^b	0.9824 (0.9823) ^b	1.0000 (1.0000) ^b
ν_2	A'	NN+GeN stretch	1165.4 (1159.2)	454.7 (479.1)	0.9726 (0.9726)	0.9952 (0.9953)	0.9681 (0.9680)	1.0006 (1.0006)
ν_3	A'	NNO bend+NN stretch	772.5 (778.1)	19.0 (26.5)	0.9935 (0.9935)	0.9783 (0.9785)	0.9717 (0.9719)	1.0002 (1.0002)
ν_4	A'	GeN stretch+GeNN bend	465.0 (460.7)	6.4 (7.1)	0.9972 (0.9974)	0.9908 (0.9908)	0.9882 (0.9883)	1.0042 (1.0042)
ν_5	A'	GeNN bend	133.5 (130.7)	6.1 (7.3)	0.9792 (0.9792)	0.9985 (0.9986)	0.9779 (0.9779)	1.0009 (1.0009)
ν_6	A''	Out-of-plane deformation	118.0 (125.0)	5.4 (7.3)	0.9715 (0.9716)	0.9970 (0.9970)	0.9684 (0.9684)	1.0005) (1.0005)
(2) ³ G	eNNO							
ν_1	A'	NNO a-stretch	1712.2 (1714.7)	257.4 (262.1)	0.9932 (0.9933)	0.9781 (0.9780)	0.9710 (0.9711)	1.0000 (1.0000)
ν_2	A'	NNO s-stretch	1185.7 (1185.2)	274.8 (274.3)	0.9840 (0.9841)	0.9968 (0.9967)	0.9809 (0.9807)	1.0000 (1.0000)
ν_3	A'	NNO bend	621.0 (620.7)	80.6 (77.7)	0.9916 (0.9916)	0.9798 (0.9797)	0.9716 (0.9716)	1.0009 (1.0009)
ν_4	A'	GeN stretch+NNO bend	350.1 (346.4)	1.7 (2.2)	0.9935 (0.9933)	0.9932 (0.9934)	0.9868 (0.9868)	1.0041 (1.0042)
ν_5	A'	GeNN bend	113.4 (109.1)	1.7 (2.5)	0.9785 (0.9785)	0.9983 (0.9984)	0.9771 (0.9772)	1.0004 (1.0004)
ν_6	A''	Out-of-plane deformation	175.0 (185.8)	5.8 (7.1)	0.9722 (0.9728)	0.9959 (0.9950)	0.9680 (0.9676)	1.0009 (1.0009)
(2)	c^{-1} Ge- η^2 [NN(O)]							
ν_1	c - Ge- η - [NN(O)] A'	NO stretch	1549.7	450.8	0.9989	0.9785	0.9775	1.0000
- 1			(1558.5)	(459.1)	(0.9989)	(0.9786)	(0.9776)	(1.0000)
ν_2	A'	NN stretch	1190.2	18.9	0.9822	0.9881	0.9698	1.0000
			(1193.9)	(20.0)	(0.9823)	(0.9880)	(0.9699)	(1.0000)
ν_3	A'	NNO bend	795.0	22.7	0.9836	0.9932	0.9765	1.0001
	A./	C-NN	(790.5)	(24.0)	(0.9839)	(0.9928)	(0.9764)	(1.0001)
ν_4	A'	GeNN s-stretch	526.0 (513.9)	20.5 (20.2)	0.9867 (0.9863)	0.9906 (0.9909)	0.9781 (0.9780)	1.0037 (1.0037)
1/-	A'	GeNN bend	300.3	12.1	0.9933	0.9932	0.9868	1.0025
ν_5	71	Gervir bend	(293.6)	(11.9)	(0.9933)	(0.9932)	(0.9868)	(1.0025)
ν_6	A''	Out-of-plane deformation	422.5 (413.6)	2.0 (1.7)	0.9992 (0.9991)	0.9741 (0.9741)	0.9733 (0.9733)	1.0002 (1.0002)
			(113.0)	(1.7)	(0.5551)	(0.5711)	(0.5755)	(1.0002)
	c^{-1} Ge- η^2 (NNO)							
ν_1	A'	NN stretch	1654.4 (1682.2)	201.3 (199.3)	0.9831 (0.9831)	0.9835 (0.9835)	0.9663 (0.9662)	1.0000 (1.0000)
ν_2	A'	NO stretch	847.3 (861.0)	52.8 (60.1)	0.9978 (0.9977)	0.9900 (0.9898)	0.9877 (0.9875)	1.0001 (1.0000)
ν_3	A'	NNO bend	660.7 (655.8)	26.2	0.9885	0.9804 (0.9804)	0.9692 (0.9694)	1.0001
ν_4	A'	GeO stretch	360.9	(25.8) 10.6	(0.9887) 0.9988 (0.0002)	0.9994	0.9981	(1.0001) 1.0030 (1.0033)
ν_5	A'	GeN stretch	(329.2) 250.0	(11.4)	(0.9992) 0.9803	(0.9993) 0.9961	(0.9984) 0.9768	(1.0033) 1.0035
ν_6	A''	Out-of-plane deformation	(214.5) 429.7	(1.9) 5.4	(0.9798) 0.9913	(0.9964) 0.9824	(0.9766) 0.9736	(1.0031) 1.0002
			(417.3)	(4.6)	(0.9916)	(0.9822)	(0.9736)	(1.0002)

TABLE II. (Continued.)

			Absorption		Isotopic ratio ^a			
ν_i	Symmetry	Mode	σ (cm ⁻¹)	IR intensities	¹⁵ N ¹⁴ NO	¹⁴ N ¹⁵ NO	¹⁵ N ¹⁵ NO	⁷² Ge
(5) ³ C	JeONN							
ν_1	A'	NNO a-stretch	2345.9	461.6	0.9889	0.9790	0.9675	1.0000
. 1			(2349.3)	(495.3)	(0.9891)	(0.9789)	(0.9676)	(1.0000)
ν_2	A'	NNO s-stretch	1295.8	113.9	0.9881	0.9979	0.9864	1.0000
2			(1302.1)	(110.4)	(0.9879)	(0.9981)	(0.9863)	(1.0000)
ν_3	A'	NNO bend	601.4	3.3	0.9943	0.9773	0.9715	1.0000
,			(576.8)	(3.0)	(0.9944)	(0.9773)	(0.9716)	(1.0000)
ν_4	A'	GeO stretch	115.6	8.0	0.9969	0.9974	0.9942	1.0022
-			(114.1)	(6.5)	(0.9970)	(0.9970)	(0.9939)	(1.0024)
ν_5	A'	GeON bend	56.4	0.2	0.9842	0.9951	0.9797	1.0035
5			(53.7)	(0.2)	(0.9832)	(0.9957)	(0.9791)	(1.0031)
ν_6	A''	Out-of-plane deformation	593.6	4.2	0.9939	0.9771	0.9709	1.0000
0			(559.5)	(5.9)	(0.9940)	(0.9771)	(0.9710)	(1.0000)
(6) ¹ G	GeONN							
ν_1	A'	NNO a-stretch	2346.8	390.9	0.9884	0.9793	0.9673	1.0000
			(2353.5)	(390.0)	(0.9886)	(0.9791)	(0.9674)	(1.0000)
ν_2	A'	NNO s-stretch	1256.7	82.5	0.9884	0.9976	0.9865	1.0000
			(1275.9)	(110.6)	(0.9883)	(0.9977)	(0.9864)	(1.0000)
ν_3	A'	NNO bend	527.5	52.5	0.9936	0.9784	0.9718	1.0000
			(510.1)	(24.7)	(0.9936)	(0.9780)	(0.9715)	(1.0000)
ν_4	A'	GeO stretch	146.8	17.9	0.9951	0.9982	0.9931	1.0015
			(140.5)	(16.7)	(0.9966)	(0.9976)	(0.9941)	(1.0020)
ν_5	A'	GeON bend	59.5	0.0	0.9878	0.9931	0.9813	1.0044
			(58.5)	(0.0)	(0.9860)	(0.9941)	(0.9805)	(1.0038)
ν_6	A''	Out-of-plane deformation	586.0	3.1	0.9938	0.9770	0.9707	1.0000
			(556.4)	(5.2)	(0.9939)	(0.9771)	(0.9708)	(1.0000)
(7) ¹ G	GeNON							
ν_1	A'	Terminal NO stretch	2000.2	1305.7	1.0000	0.9819	0.9819	1.0000
			(2014.6)	(1337.8)	(1.0000)	(0.9819)	(0.9819)	(1.0000)
ν_2	A'	GeN stretch	976.8	261.7	0.9711	1.0000	0.9711	1.0019
			(968.5)	(252.5)	(0.9710)	(1.0000)	(0.9710)	(1.0018)
ν_3	A'	NON bend	496.1	52.8	0.9957	0.9919	0.9876	1.0001
			(487.1)	(52.5)	(0.9958)	(0.9920)	(0.9878)	(1.0001)
ν_4	A'	Central NO stretch	231.7	30.4	0.9991	0.9846	0.9837	1.0032
			(231.8)	(26.9)	(0.9992)	(0.9844)	(0.9836)	(1.0032)
ν_5	A'	GeNO bend	37.4	21.3	0.9751	0.9953	0.9704	1.0008
			(30.6)	(25.7)	(0.9746)	(0.9961)	(0.9708)	(1.0010)
ν_6	A''	Out-of-plane deformation	12.8	25.5	0.9886	0.9738	0.9627	1.0018
			(36.3)	(31.0)	(0.9729)	(0.9943)	(0.9670)	(1.0002)

^aThe isotopic ratio is defined as the ratio of vibrational wavenumber of the specific isotopic variant to that of the naturally abundant species, in this case, species containing ⁷⁴Ge, ¹⁴N, and ¹⁶O.

In summary, the results of computations indicate that reactions of ${}^3\text{Ge}$ with N_2O likely lead to formation of ${}^3\text{Ge}\text{ONN}$ and ${}^3\text{Ge}\text{NNO}$; the latter is expected to relax to ${}^1\text{Ge}\text{NNO}$ under low-temperature matrix conditions. Other isomers such as ${}^1\text{Ge}\text{NON}$ or $cyc^{-3}\text{Ge}-\eta^2$ (NNO) are unlikely to be produced because the reaction must overcome a large barrier. $cyc^{-3}\text{Ge}-\eta^2$ (NNO) might not be observed because the barrier for the decay into ${}^3\text{Ge}\text{O}+\text{N}_2$ is small. The probability to produce $cyc^{-1}\text{Ge}-\eta^2$ [NN(O)] directly in experiments with codeposition of ${}^3\text{Ge}+\text{N}_2\text{O}$ might be small because we are unable to locate any direct path connecting ${}^3\text{Ge}+\text{N}_2\text{O}$ with $cyc^{-1}\text{Ge}-\eta^2$ [NN(O)].

VI. DISCUSSION

A. Assignment of observed new features in group A to $^{1}\text{GeNNO}$

From the ¹⁵N-isotopic substitution experiments (Fig. 3), the new species clearly contains two N atoms; all three main vibrational lines near 1443.7, 1102.4, and 784.0 cm⁻¹ involve inequivalent motions from these two N atoms because no observed isotopic shift is identical. The possibility of this species being GeNN is readily excluded because we expect a much larger vibrational wavenumber for the N=N stretching mode of GeNN, as confirmed from quantum-chemical

^bValues calculated with B3LYP/6-311+G(d,p) are listed in parentheses.

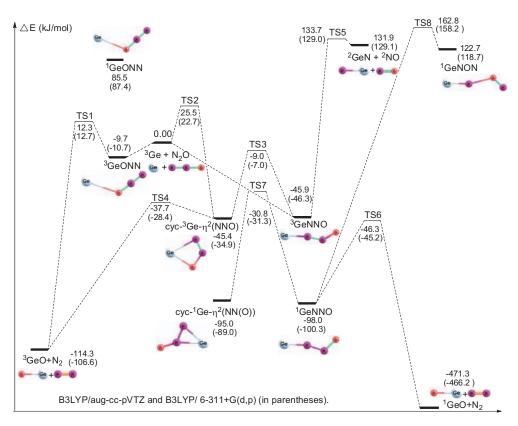


FIG. 5. GeN_2O potential energy computed with B3LYP/aug-cc-pVTZ and B3LYP/6-311+G(d,p) methods. Relative energies are in kJ mol^{-1} ; those derived with B3LYP/6-311+G(d,p) are listed in parentheses.

calculations;²¹ other isomers of GeN₂, cyc-GeN₂, and NGeN have equivalent N atoms and vibrational wavenumbers unmatched with our observation. Hence, the likely carrier of these new features is expected to be one isomer of GeN₂O.

By comparison with computed vibrational wavenumbers listed in Table II, only two candidates have a vibrational mode with wavenumbers similar to our observation: 1 GeNNO (1511, 1165, and 773 cm $^{-1}$ from B3LYP/aug-ccpVTZ) and cyc^{-1} Ge- η^{2} [NN(O)] (1550, 1190, and 795 cm $^{-1}$); other isomers have corresponding vibrational wavenumbers predicted to be at least 210 cm $^{-1}$ greater than the observed value. However, the IR intensity distributions differ markedly for these two species. 1 GeNNO is predicted to have two intense lines, with that near 1165 cm $^{-1}$ nearly twice as intense as that near 1511 cm $^{-1}$. In contrast, the line at 1550 cm $^{-1}$ for cyc^{-1} Ge- η^{2} [NN(O)] is more than 20 times as intense as other lines. Our observed relative intensities of lines at 1443.7 and 1102.4 cm $^{-1}$ (Figs. 2 and 3) are consistent with those predicted for 1 GeNNO.

The 15 N-isotopic ratios provide further support for the assignments to 1 GeNNO. The isotopic ratio is defined as the ratio of vibrational wavenumber of the specific isotopic variant to that of the naturally abundant species, in this case, species containing 74 Ge, 14 N, and 16 O. Observed isotopic ratios are listed parenthetically in Table I to compare with those derived from quantum-chemical calculations in Table II; they agree satisfactorily with those of 1 GeNNO, with deviations less than 0.0023. The agreement is much worse for cyc^{-1} Ge- η^{2} [NN(O)] with deviations as much as 0.0135.

Computations predict a shift of the ν_3 line of $cyc^{-1}Ge^{-\eta^2}$ [$^{14}N^{15}N(O)$] much smaller than $cyc^{-1}Ge^{-\eta^2}$ [$^{15}N^{14}N(O)$], but our observation indicates the reverse.

For convenience, we also list observed and computed isotopic shifts in Table III. We assign the line at 1443.7 cm⁻¹ to ν_1 of $^1\text{GeNNO}$; the vibrational wavenumber is consistent with a NO-stretching mode. The observed ^{15}N -isotopic shifts indicate that mainly the central N atom of the NNO moiety is involved in this vibration because these lines observed from reactions of Ge with $^{14}\text{N}^{15}\text{NO}$ and $^{15}\text{N}^{15}\text{NO}$ show shifts $(\Delta\nu=-22.1 \text{ and } -26.0 \text{ cm}^{-1}, \text{ respectively})$ much greater than that $(\Delta\nu=-3.5 \text{ cm}^{-1})$ with $^{15}\text{N}^{14}\text{NO}$.

We assign the line at 1102.4 cm⁻¹ to the ν_2 mode of ¹GeNNO. The observed ¹⁵N-isotopic shifts indicate that this vibration mainly involves the terminal N atom rather than the central N atom of the NNO moiety because lines near 1102 cm⁻¹ observed from reactions of Ge with ¹⁵N¹⁴NO and $^{15}\mathrm{N}^{15}\mathrm{NO}$ show shifts ($\Delta \nu = -27.7$ and -33.0 cm⁻¹, respectively) much greater than that $(\Delta \nu = -5.6 \text{ cm}^{-1})$ with ¹⁴N¹⁵NO. As the GeN stretching mode is expected to show a smaller wavenumber like that predicted at 868.5 cm⁻¹ for H₂GeNH, 46 this observed mode must be mixed with NN stretching. If only GeN stretch were involved in this mode, we would expect to observe splitting due to Ge isotopes. The vector displacements computed for this mode confirm this mixing. According to the computations, the absorption lines of the ⁷⁴Ge- and ⁷²Ge-isotopic species shift by only -0.7 cm⁻¹, not enough for us to resolve these lines. The unresolved Ge-isotopic variants might be the cause of a

TABLE III. Comparison of observed isotopic shifts with those predicted for isomers of GeN_2O with B3LYP/aug-cc-pVTZ and B3LYP/6-311+G(d,p).

			$\sigma^{ m \ a}$		Isotopic shift	
Species	ν_i observed		(cm ⁻¹)	¹⁵ N ¹⁴ NO	¹⁴ N ¹⁵ NO	¹⁵ N ¹⁵ NO
¹ GeNNO	$ u_1$	Expt.	1443.7	-3.5	-22.1	-26.0
		Calc.	1510.6	-2.4	-23.9	-26.7
			$(1523.5)^{b}$	$(-2.3)^{b}$	$(-24.3)^{b}$	$(-26.9)^{b}$
	$ u_2$	Expt.	1102.4	-27.7	-5.6	-33.0
		Calc.	1165.4	-31.9	-5.5	-37.2
			(1159.2)	(-31.8)	(-5.5)	(-37.1)
	ν_3	Expt.	784.0	-5.3	-15.9	-21.3
		Calc.	772.5	-5.0	-16.8	-21.8
			(778.1)	(-5.1)	(-16.7)	(-21.9)
	$\nu_3 + \nu_4$	Expt.	1241.8	-7.3	-19.1	-26.7
			1239.7	-7.2	-18.9	-26.6
			1238.1	-7.3	-18.8	-26.6
		Calc.	1237.5	-6.3	-21.1	-27.3
			(1238.8)	(-6.3)	(-21.0)	(-27.2)
	$2\nu_1$	Expt.	2859.2	-8.3	-42.6	-51.2
		Calc.	3021.2	-4.8	-47.7	-53.3
			(3047.0)	(-4.5)	(-48.6)	(-53.8)
³ GeONN	$ u_2$	Expt.	1259.3	-14.7	-4.7	-18.7
			1255.5	-13.7	-4.6	-18.4
		Calc.	1295.8	-15.4	-2.7	-17.6
			(1302.1)	(-15.8)	(-2.5)	(-17.8)
$cyc^{-1}Ge^{-\eta^2}$ [NN(O)]	$ u_1$	Expt.	1488.9	-2.2	-30.2	-32.5
			1486.4	-2.2	-30.2	-32.3
		Calc.	1549.7	-1.7	-33.3	-34.9
			(1558.5)	(-1.7)	(-33.3)	(-35.0)

^aVibrational wavenumber of the naturally abundant species containing ⁷⁴Ge, ¹⁴N, and ¹⁶O.

width of 2.7 cm⁻¹ for the feature at 1102.4 cm⁻¹, much greater than that (1.2 cm⁻¹) of the feature at 1443.7 cm⁻¹.

The 784.0 cm⁻¹ vibration is assigned as mainly the NNO bending (ν_3) mode. The observed ¹⁵N-isotopic shifts indicate that this vibration mainly involves the central N atom rather than the terminal one of the NNO moiety because these features observed from reactions of Ge with ¹⁴N¹⁵NO and ¹⁵N¹⁵NO show shifts ($\Delta\nu$ =-15.9 and -21.3 cm⁻¹, respectively) much greater than that ($\Delta\nu$ =-5.3 cm⁻¹) with ¹⁵N¹⁴NO. From the computed vector displacements, we assign this mode as NNO bend mixed with some NN stretch. The observed vibrational wavenumber of this mode is slightly greater than the computed value of 772.5 cm⁻¹, likely because of negative anharmonicity of the bending mode; a similar trend was observed for SiNNO.²⁰

Two additional features near 2859.2 and 1238.1 cm⁻¹ were also identified to belong to group A. The line at 2859.2 cm⁻¹ is readily assigned to $2\nu_1$, with an anharmonicity of $\omega_e x_e = 14.1$ cm⁻¹ for ⁷⁴Ge¹⁴N¹⁴N¹⁶O. Corresponding lines observed at 2850.9, 2816.6, and 2808.0 cm⁻¹ for Ge¹⁵N¹⁴NO, Ge¹⁴N¹⁵NO, and Ge¹⁵N¹⁵NO (Fig. 6) show ¹⁵N-isotopic shifts roughly twice as large as those observed for ν_1 , supporting the assignment of this feature to $2\nu_1$.

The feature near 1238.1 cm⁻¹ for ¹GeNNO and the corresponding features for various ¹⁵N substituted species are shown in Fig. 7. The splitting due to ⁷⁰Ge, ⁷²Ge, and ⁷⁴Ge is barely resolvable. For Ge¹⁴N¹⁴N¹⁶O they are deconvoluted

to have maxima at 1241.8, 1239.7, and 1238.1 cm⁻¹; the two components from 73 Ge and 76 Ge species are too weak to be discernible. This feature hence involves the GeN stretching mode, which has contributions to the ν_2 and ν_4 modes. From computed harmonic wavenumbers of six vibrational modes of 1 GeNNO, this feature at 1238.1 cm⁻¹ is readily assigned as the $\nu_3 + \nu_4$ combination; ν_3 is observed at 784.0 cm⁻¹, and ν_4 is computed to be near 465 cm⁻¹. Observed 15 N-isotopic ratios are consistent with those computed from harmonic

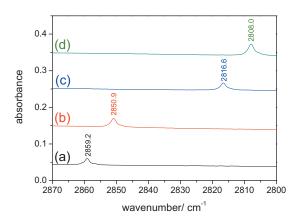


FIG. 6. Partial IR spectrum in the range $2800-2870~{\rm cm^{-1}}$ showing absorption of the $2\nu_1$ line of $^1{\rm GeNNO}$ after codeposition of Ge vapor with various $^{15}{\rm N}$ -labeled N₂O: (a) $^{14}{\rm N}^{14}{\rm NO}$, (b) $^{15}{\rm N}^{14}{\rm NO}$, (c) $^{14}{\rm N}^{15}{\rm NO}$, and (d) $^{15}{\rm N}^{15}{\rm NO}$.

^bValues calculated with B3LYP/6-311+G(d,p) are listed in parentheses.

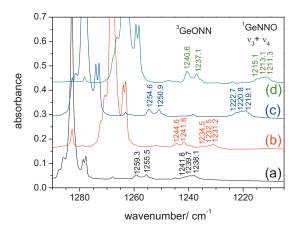


FIG. 7. Partial IR spectrum in the range $1210-1290 \text{ cm}^{-1}$ after codeposition of Ge vapor with various $^{15}\text{N-labeled N}_2\text{O}$: (a) $^{14}\text{N}^{14}\text{NO}$, (b) $^{15}\text{N}^{14}\text{NO}$, (c) $^{14}\text{N}^{15}\text{NO}$, and (d) $^{15}\text{N}^{15}\text{NO}$. The doublets located near the ν_2 fundamental of N₂O are assigned to $^3\text{GeONN}$. The features to the right showing a typical Ge isotope splitting pattern are assigned to the $\nu_3+\nu_4$ lines of $^1\text{GeNNO}$

wavenumbers of the combination. Furthermore, the computed splitting for $\nu_3 + \nu_4$ between singlet ⁷⁰GeNNO and ⁷²GeNNO is 2.2 cm⁻¹, consistent with observed splitting of 2.1 cm⁻¹.

Upon irradiation at 254 nm (low-pressure Hg lamp) or 248 nm (KrF laser), lines of all ${\rm GeN_2O}$ isomers diminished, and the GeO product was observed. We had hoped to open a second reaction channel by applying the 193 nm emission from an ArF laser, but no indication of the formation of another isomer of ${\rm GeN_2O}$ or dissociation product such as GeN or NO was observed.

B. Tentative assignment of observed new features in group B to ³GeONN

According to our computations, ${}^3\text{GeONN}$ is expected to be directly formed from ${}^3\text{Ge}$ and $N_2\text{O}$. Notably, the NNO a-stretching (ν_1) vibration is predicted to show a blueshift, whereas the NNO s-stretching (ν_2) vibration is predicted to show a redshift relative to $N_2\text{O}$. Near the $N_2\text{O}$ s-stretching vibration of $N_2\text{O}$, a new doublet at 1259.3 and 1255.5 cm⁻¹ was observed, as depicted in Fig. 7. No new feature was positively identified near the a-stretching region of $N_2\text{O}$, likely because of interference by several extra lines of $N_2\text{O}$ caused by the matrix effect.

The only species listed in Table II that has a vibrational band near 1255 cm⁻¹ is 3 GeONN. Observed 15 N-isotopic ratios (Table I) deviate from those computed quantum chemically (Table II) by less than 0.0016. Hence, we tentatively assign this feature to the ν_2 mode of 3 GeONN. The reason for the doublet structure is unclear, likely due to different matrix environments.

C. Tentative assignment of observed new features in group C to $cyc^{-1}Ge^{-\eta^2}[NN(O)]$

We detected weak signals at 1488.9 and 1486.4 cm⁻¹, as shown in Fig. 8, which belong to neither 1 GeNNO nor 3 GeONN according to their photochemical behavior. From its photochemical behavior, production with $\lambda > 525\,$ nm, we

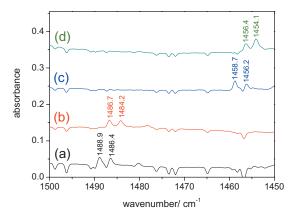


FIG. 8. Partial IR spectrum in the range $1450-1500 \text{ cm}^{-1}$ after codeposition of Ge vapor with various $^{15}\text{N-labeled N}_2\text{O}$: (a) $^{14}\text{N}^{14}\text{NO}$, (b) $^{15}\text{N}^{14}\text{NO}$, (c) $^{14}\text{N}^{15}\text{NO}$, and (d) $^{15}\text{N}^{15}\text{NO}$. The weak doublets are tentatively assigned to $cyc^{-1}\text{Ge-}\eta^2$ [NN(O)].

derive that this species is closely related to 1 GeNNO. These features are tentatively associated with the NO stretching (ν_{1}) mode of cyc^{-1} Ge- η^{2} [NN(O)], the second most stable isomer, according to the computed vibrational wavenumbers, IR intensities, and 15 N-isotopic ratios. The observed 15 N-isotopic ratios (Table I) deviate from those computed quantum chemically (Table II) by less than 0.0012. ν_{1} is the only vibrational mode of cyc^{-1} Ge- η^{2} [NN(O)] that has significant IR intensity for detection.

According to quantum-chemical computations, we found no reaction path that yielded directly $cyc^{-1}Ge^{-\eta^2}$ [NN(O)] under our experimental conditions. This is consistent with the extremely small intensity observed for this feature.

VII. CONCLUSION

We codeposited Ge metal vapor and N2O in Ar onto a substrate at 11 K and observed lines in three groups that exhibit distinct photochemical behaviors. The group with the most intense features is assigned to absorption of ¹GeNNO; intense lines at 1443.7, 1102.4, and 784.0 cm⁻¹ are assigned as ν_1 , ν_2 , and ν_3 , whereas weak lines at 1238.1 and 2859.2 cm⁻¹ are assigned as $\nu_3 + \nu_4$ and $2\nu_1$, respectively. A weak doublet at 1255.5 and 1259.3 cm⁻¹ is tentatively assigned as ν_2 of ³GeONN, and another weak doublet at 1486.4 and 1488.9 cm⁻¹ is tentatively assigned to the ν_1 mode of $cyc^{-1}Ge^{-\eta^2}$ [NN(O)]. Observed vibrational wavenumbers, relative IR intensities, and ¹⁵N-isotopic ratios are consistent with those computed quantum chemically. The formation of ¹GeNNO is the major channel; Ge reacts with N₂O to form ³GeNNO followed by relaxation to the more stable ¹GeNNO.

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